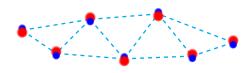
Ultracold molecule assembly

Yichao Yu

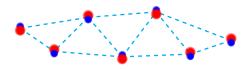
Ni Group/Harvard

Aug 11, 2017

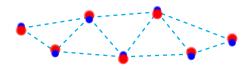
- Strong and tunable interaction
- Rich internal energy levels
- High filling fraction
- Single site detection and manipulation



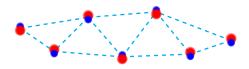
- Strong and tunable interaction
- Rich internal energy levels
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- Single site detection and manipulation



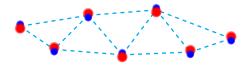
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- Strong and tunable interaction
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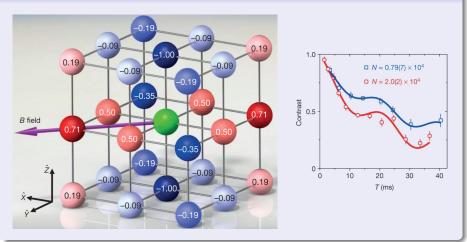


- Strong and tunable interaction
- Rich internal energy levels
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- Single site detection and manipulation



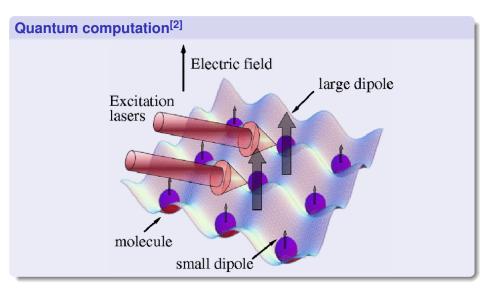
Applications

Simulation of many-body system^[1]



[1] B. Yan et al., "Observation of dipolar spin-exchange interactions with lattice-confined polar molecules.", Nature **501**, 521–5 (2013).

Applications

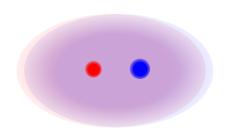


[2] S. F. Yelin et al., "Schemes for robust quantum computation with polar molecules", 4 (2006).

- MOT (Na + Cs)
- Loading single atoms
- Raman sideband cooling
- Merge traps
- Make molecules!



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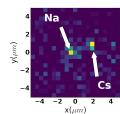
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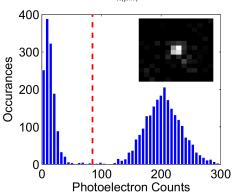
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Atom loading and cooling

Single atoms

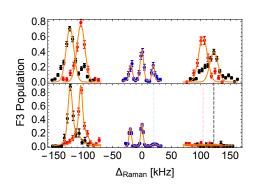
 85% cround state after Cesium Raman sideband cooling



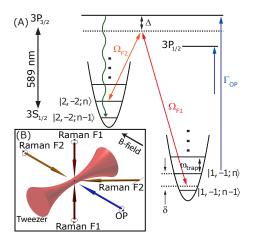


Atom loading and cooling

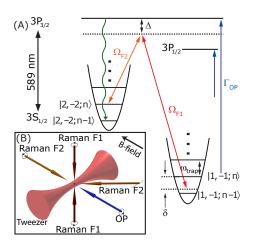
- Single atoms
- 85% cround state after Cesium Raman sideband cooling



Raman sideband cooling



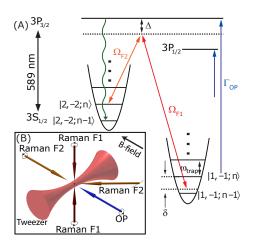
Raman sideband cooling



Difficulties

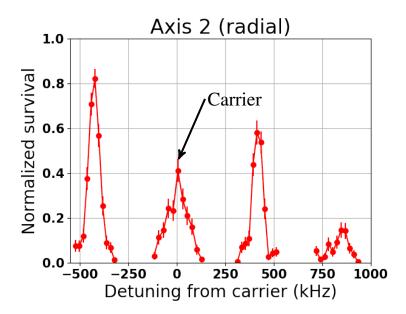
- High initial temperature $(40\mu K)$
- High recoil heating (High Lamb Dicke parameter)

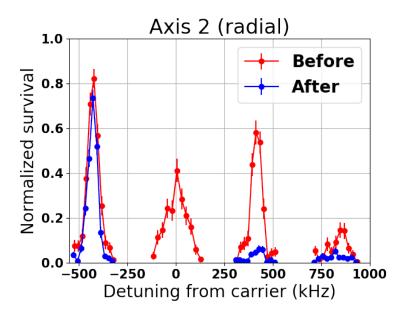
Raman sideband cooling

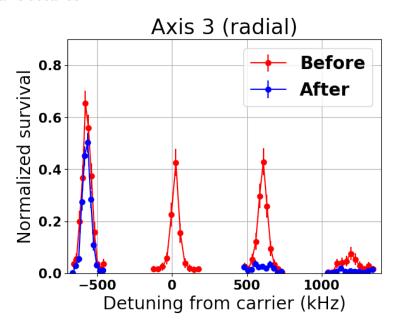


Difficulties

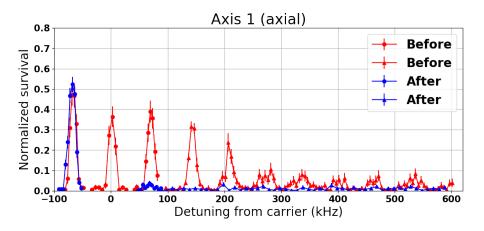
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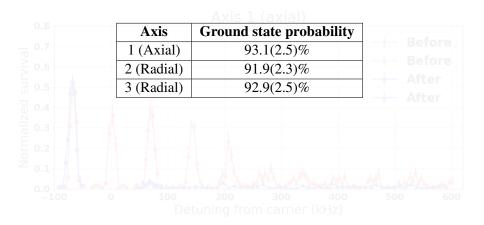










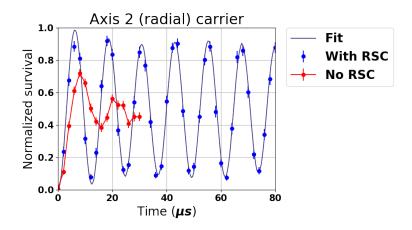


AAIS I (GAIGI)	
Axis	Ground state probability
1 (Axial)	93.1(2.5)%
2 (Radial)	91.9(2.3)%
3 (Radial)	92.9(2.5)%

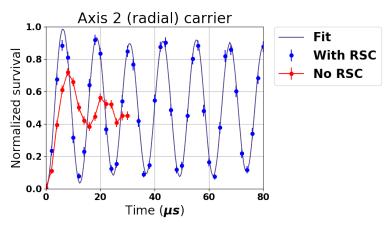
3D ground state: 79.5(3.6)%Loss after cooling: 15%

Total 3D ground state preparation fidelity: 67.6(3.1)%

Rabi flopping (radial)

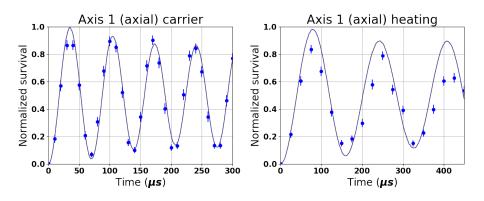


Rabi flopping (radial)

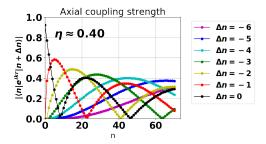


Good agreement in ground state probability between spectrum and Rabi flopping data.

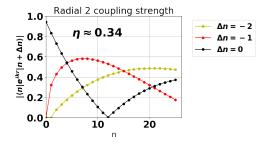
Rabi flopping (axial)



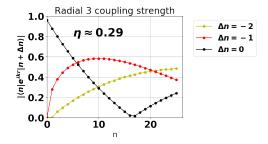
Axial matrix element



Radial 2 matrix element



Radial 3 matrix element



Next step